

Diodes

# Switching diode

## 1SS380

●Applications

Low leakage switching

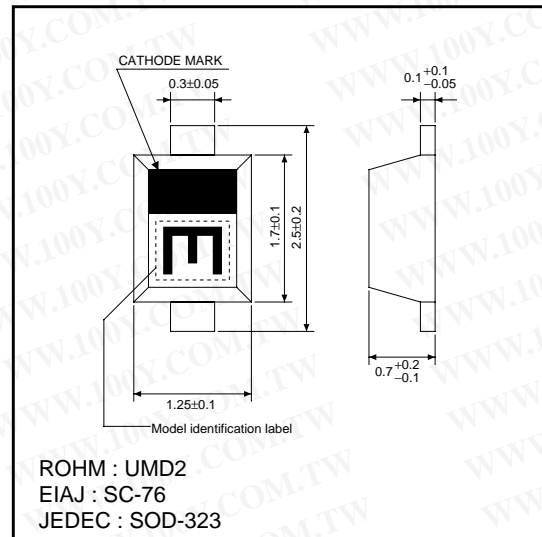
●Features

- 1) Small surface mounting type. (UMD2)
- 2) Ultra low I<sub>R</sub>. (I<sub>R</sub>=40pA Typ.)
- 3) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V <sub>RM</sub>	40	V
DC reverse voltage	V <sub>R</sub>	35	V
Peak forward current	I <sub>FM</sub>	225	mA
Mean rectifying current	I <sub>o</sub>	100	mA
Surge current (1s)	I <sub>surge</sub>	400	mA
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55~+125	°C

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>F</sub>	-	-	1.2	V	I <sub>F</sub> =100mA
Reverse current	I <sub>R</sub>	-	-	10	nA	V <sub>R</sub> =20V
Capacitance between terminals	C <sub>T</sub>	-	-	5.0	pF	V <sub>R</sub> =0.5V, f=1MHz

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●Electrical characteristic curves (Ta = 25°C)

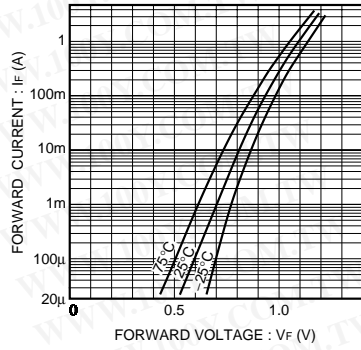


Fig. 1 Forward characteristics

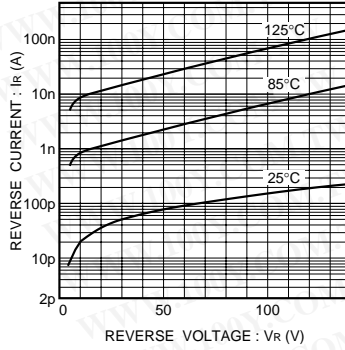


Fig. 2 Reverse characteristics

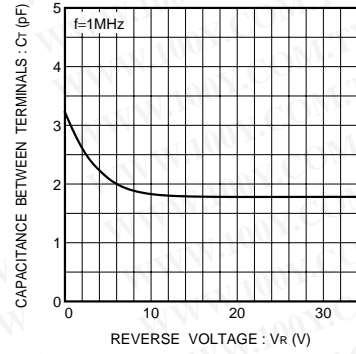


Fig. 3 Capacitance between terminals characteristics

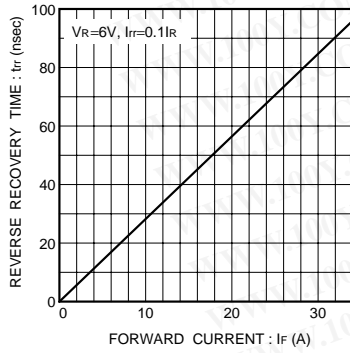


Fig. 4 Reverse recovery time characteristics

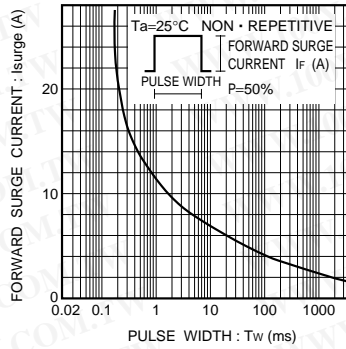


Fig. 5 Surge current characteristics

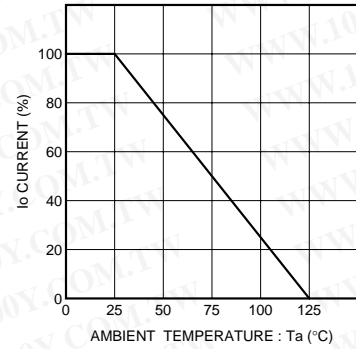


Fig. 6 Derating curve (mounting on glass epoxy PCBs)